



## **Excitonic Devices**

### Transistors, Traps, and Stirring Potentials

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# Introduction to indirect excitons



Direct

Z

 $E \bullet$ 

GaAs

Indirect

AlGaAs

Exciton: bound electron – hole pair

**Indirect exciton**: electron and hole are confined to spatially separated quantum well layers

#### **Properties of indirect excitons**

- Increased lifetime
  - Increased transport distances
  - Allows for cooling to low temperatures
- Are oriented dipoles:
  - -repulsive interaction screens disorder
  - -exciton energy is controllable by voltage  $E = edF_z$

**Excitonic Devices** 

Physics of Cold Bosons in Materials

Yesterday in 210B

Today 12:30 in

**210B** 

## **Excitonic devices**



• Traps for excitons

A.A. High *et al, PRL* 2009A.A. High *et al, Nano Lett* 2009Y.Y. Kuznetsova *et al, APL* 2010A.A. High *et al, Nano Lett.* 2012

• Lattices for excitons



M. Remeika *et al, PRL* 2009 M. Remeika *et al, APL* 2012

• Excitonic conveyer, CCD



A.G. Winbow et al, PRL 2011

#### • Excitonic circuits



A.G. Winbow et al, Nano Lett. 2007
A.A. High et al, Opt. Lett. 2007
A.G. Winbow et al, JAP 2008
A.A. High et al, Science 2008
G. Grosso et al, Nature Phot. 2009
Y.Y. Kuznetsova et al, Opt. Lett. 2010
J.R. Leonard et al, APL 2012

# Overview

- Excitonic Transistors
- Snowflake Traps for Excitons
- Stirring Potentials for Excitons

## **Excitonic transistors**

- Geometry similar to FET
- Time delay between signal processing and optical communication is effectively eliminated
- Compact footprint



#### Exciton optoelectronic transistor



Source and drain are photonic; Exciton flux from source to drain is controlled by voltage on gate electrode

A.A. High *et al, Optics Lett.* 2007 A.A. High *et al, Science* 2008 G. Grosso *et al, Nature Phot.* 2009

#### All-optical excitonic transistor



Source and drain are photonic. Light changes voltage at gate electrode, controlling exciton flux from source to drain.

Y.Y. Kuznetsova et al, Optics Lett. 2010



P. Andreakou et al, APL 2014



Ramp: exciton transport in the direction of lower potential energy

→ realizes directed transport of excitons analogous to a diode for electrons

J.R. Leonard *et al, APL* 2012

#### Y.Y. Kuznetsova et al, APL 2010

![](_page_7_Figure_1.jpeg)

P. Andreakou et al, APL 2014

![](_page_8_Picture_1.jpeg)

#### Light controls light by using excitons as an intermediate medium.

• Single-electrode design prevents heating by in-plane electron currents

P. Andreakou, S.V. Poltavtsev, J.R. Leonard, E.V. Calman, M. Remeika, Y.Y. Kuznetsova, L.V. Butov, J. Wilkes, M. Hanson, A.C. Gossard, *Appl. Phys. Lett.* **104**, 091101 (2014)

![](_page_9_Picture_1.jpeg)

#### Light controls light by using excitons as an intermediate medium.

- Single-electrode design prevents heating by in-plane electron currents
- Also operates as a router

P. Andreakou, S.V. Poltavtsev, J.R. Leonard, E.V. Calman, M. Remeika, Y.Y. Kuznetsova, L.V. Butov, J. Wilkes, M. Hanson, A.C. Gossard, *Appl. Phys. Lett.* **104**, 091101 (2014)

![](_page_10_Figure_1.jpeg)

P. Andreakou, S.V. Poltavtsev, J.R. Leonard, E.V. Calman, M. Remeika, Y.Y. Kuznetsova, L.V. Butov, J. Wilkes, M. Hanson, A.C. Gossard, *Appl. Phys. Lett.* **104**, 091101 (2014)

# Overview

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## Diamond-Shaped Trap

![](_page_12_Figure_1.jpeg)

- Creates canoe-shaped confining potential for excitons in small area

- Only small number of excitons can be trapped

- Condensate of ~1000 exictons can be collected

A.A. High *et al, PRL* 2009 *Nano Lett.* 2012

#### Exciton potential energy in <sup>2D</sup> Snowflake trap Realization of 2D Snowflake Trap

![](_page_13_Figure_1.jpeg)

- Realization of high-density exciton gas in trap center

Outlook: Study high-density condensates in 2D snowflake traps

Green circles mark excitation spots

# Overview

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## Moving Lattice: Conveyer

![](_page_15_Figure_1.jpeg)

A.G. Winbow et al, PRL 2011

### Stirring Potential for Indirect Excitons (Carousel)

![](_page_16_Figure_1.jpeg)

•Stirring potentials can be used to generate vortices.

•Vortices are studied for various collective states, which range from superconductors to BEC.

#### **Control of Stirring Potential:**

•Angular velocity is controlled by AC frequency

•Wavelength is determined by electrode periodicity

•Potential amplitude is controlled by AC amplitude

### Design of Stirring Potential for Excitons (Carousel)

![](_page_17_Picture_1.jpeg)

Carousel electrodes

### Design of Stirring Potential for Excitons (Carousel)

![](_page_18_Picture_1.jpeg)

Carousel electrodes

Insulating layer with openings for connections

### Design of Stirring Potential for Excitons (Carousel)

![](_page_19_Picture_1.jpeg)

![](_page_20_Figure_1.jpeg)

![](_page_21_Figure_0.jpeg)

## Conclusions

- Demonstrated an all-optical excitonic transistor and router
- Demonstrated a 2D snowflake trap for excitons

• Demonstrated a stirring potential for excitons

![](_page_22_Picture_4.jpeg)

![](_page_22_Picture_5.jpeg)

![](_page_22_Picture_6.jpeg)

![](_page_22_Figure_7.jpeg)